Philips Semiconductors

Product specification

Triacs MAC223A8X

GENERAL DESCRIPTION

Passivated triac in a full pack, plastic envelope, intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

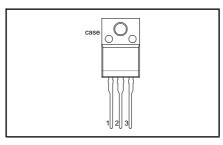
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{DRM}	Repetitive peak off-state voltages	600	V
I _{T(RMS)}	RMS on-state current	20	Α
I _{TSM}	Non-repetitive peak on-state current	230	Α

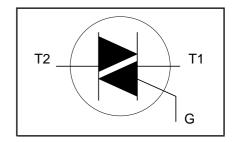
PINNING - SOT186A

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
case	isolated

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DRM}	Repetitive peak off-state voltages		-	600 ¹	\ \
I _{T(RMS)}	RMS on-state current Non-repetitive peak on-state current	full sine wave; $T_{hs} \le 25 ^{\circ}C$ full sine wave; $T_j = 25 ^{\circ}C$ prior to surge	-	20	А
		t = 16.7 ms	-	230	A A ² s
l²t dl _⊤ /dt	l ² t for fusing Repetitive rate of rise of on-state current after	t = 10 ms $I_{TM} = 30 \text{ A}; I_G = 0.2 \text{ A};$ $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$	-	180	A ² s
	triggering	<u>T</u> 2+ G+	-	50	A/μs
		T2+ G-	-	50	A/μs
		T2- G- T2- G+	-	50 10	A/μs
1	Peak gate current	12- 9+	1 -	10 2	A/μs A
$oldsymbol{V}_GM$	Peak gate voltage		_	5	V
P _{GM}	Peak gate power		-	5 5	Ŵ
P _{G(AV)}	Average gate power	over any 20 ms period	-	0.5	W
$\begin{bmatrix} T_{stg} \\ T_{j} \end{bmatrix}$	Storage temperature Operating junction temperature		-40 -40	150 125	သို

Philips Semiconductors Product specification

Triacs MAC223A8X

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-hs}	Thermal resistance junction heatsink	full or half cycle with heatsink compound without heatsink compound	-	-	3.85 5.5	K/W K/W
R _{th j-a}	Thermal resistance junction to ambient	in free air	-	55	-	K/W

ISOLATION LIMITING VALUE & CHARACTERISTIC

 T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	R.M.S. isolation voltage from all three terminals to external heatsink	f = 50-60 Hz; sinusoidal waveform; R.H. ≤ 65%; clean and dustfree	-	-	2500	V
C _{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	-	10	-	pF

STATIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
I _{GT}	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$					
•			T2+ G+	-	6	50	mΑ
			T2+ G-	-	10	50	mΑ
			T2- G-	-	11	50	mA
			T2- G+	-	23	75	mA
l _L	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$			_		_
			T2+ G+	-	8	40	mA
			T2+ G-	-	30	60	mĄ
			T2- G-	-	18	40	mA
١.	LIALPAN STATE	101/1 04.4	T2- G+	-	15	60	mA
I _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	то.		7	20	Л
			T2+	-		30	mA m^
l 🗤	On state valtage	1 20 4	T2-	-	12	30	mA V
V_{T}	On-state voltage	$I_T = 30 \text{ A}$		-	1.3 0.7	1.55	V
v _{GT}	Gate trigger voltage	$ V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	°C	0.25	0.7	1.5	V
1.	Off-state leakage current	$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 $ $V_D = V_{DRM(max)}; T_j = 125 ^{\circ}\text{C}$	C	0.25	0.4	0.5	
I _D	Ton-state leakage current	$\mathbf{v}_{\mathrm{D}} = \mathbf{v}_{\mathrm{DRM(max)}}, \mathbf{I}_{\mathrm{j}} = 125 \mathrm{C}$		_	U. I	0.5	mA

DYNAMIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV _D /dt	Critical rate of rise of	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125 °C;$	100	300	-	V/μs
dV _{com} /dt	off-state voltage Critical rate of change of commutating voltage	exponential waveform; gate open circuit $V_{DM} = 400 \text{ V}$; $T_j = 95 ^{\circ}\text{C}$; $I_{T(RMS)} = 25 \text{ A}$; $dI_{com}/dt = 9 \text{ A/ms}$; gate open circuit	-	10	-	V/μs
t _{gt}	Gate controlled turn-on time	$I_{TM} = 30 \text{ A}; V_D = V_{DRM(max)}; I_G = 0.1 \text{ A};$ $I_{G} = 5 \text{ A/}\mu\text{s}$	-	2	-	μs

Philips Semiconductors Product specification

Triacs MAC223A8X

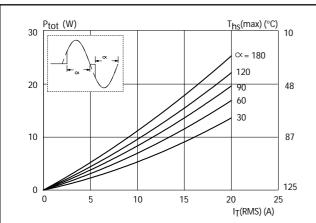


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where $\alpha = conduction$ angle.

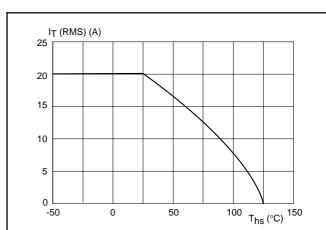


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus heatsink temperature T_{hs} .

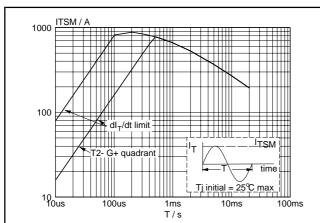


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 20$ ms.

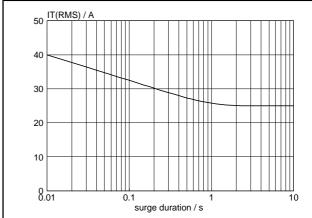


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{hs} \le 91$ °C.

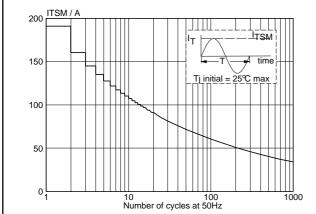


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

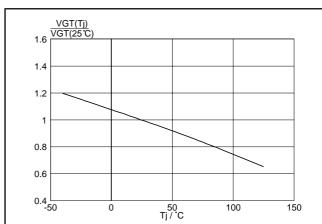
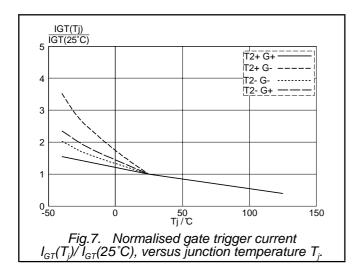
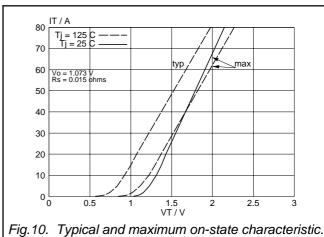


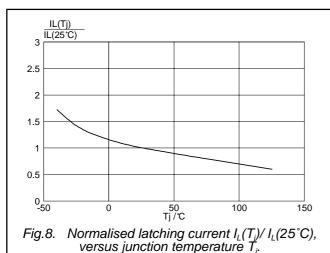
Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/V_{GT}(25^{\circ}C)$, versus junction temperature T_{j} .

Philips Semiconductors Product specification

Triacs MAC223A8X







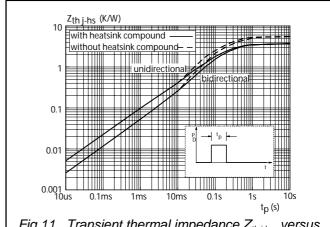


Fig.11. Transient thermal impedance $Z_{th j-hs}$, versus pulse width t_p .

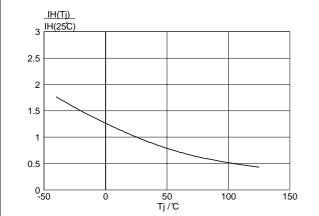


Fig.9. Normalised holding current $I_H(T_i)/I_H(25^{\circ}\text{C})$, versus junction temperature T_j .

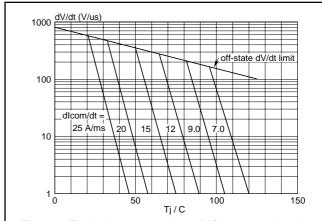
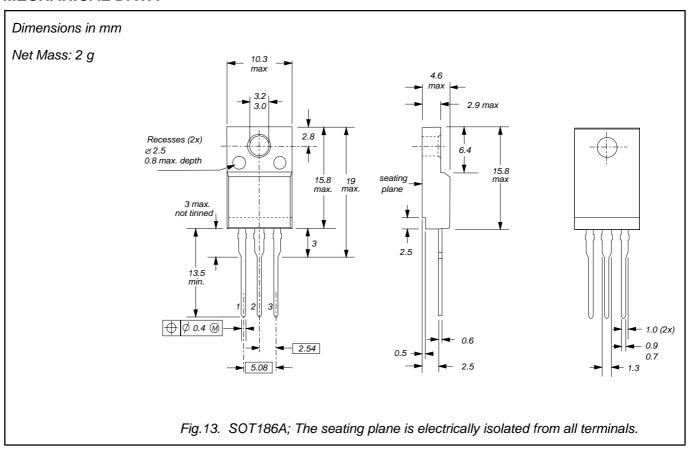


Fig.12. Typical commutation dV/dt versus junction temperature, parameter commutation dl_T/dt. The triac should commutate when the dV/dt is below the value on the appropriate curve for pre-commutation dI_{τ}/dt .

Philips Semiconductors Product specification

MAC223A8X **Triacs**

MECHANICAL DATA



- Notes
 1. Refer to mounting instructions for F-pack envelopes.
 2. Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

Triacs MAC223A8X

DEFINITIONS

DATA SHEET STATU	DATA SHEET STATUS					
DATA SHEET STATUS ¹	PRODUCT STATUS ²	DEFINITIONS				
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice				
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product				
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A				

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

© Philips Electronics N.V. 2002

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, it is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent or other industrial or intellectual property rights.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

September 2002 6 Rev 1.000

-

¹ Please consult the most recently issued datasheet before initiating or completing a design.

² The product status of the device(s) described in this datasheet may have changed since this datasheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.